



DMG302PU

25V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C
-25V	10Ω @ V _{GS} = -4.5V	-0.17A
	13Ω @ V _{GS} = -2.7V	-0.15A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surfaced Mount Package
- ESD Protected Gate (>6kV Human Body Model)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

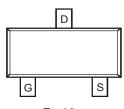
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 @3
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

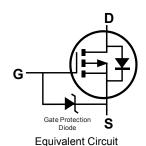








Top View Pin Configuration



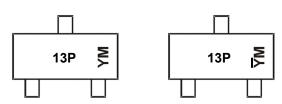
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMG302PU-7	Standard	SOT23	3,000/Tape & Reel
DMG302PU-13	Standard	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



13P = Product Type Marking Code

 \underline{Y} M = Date Code Marking for SAT (Shanghai Assembly/ Test site) \overline{Y} M = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Υ		Z		Α	Е	3	С		D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	V			
Gate-Source Voltage	V_{GSS}	-8	V		
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-0.17 -0.14	Α
Continuous Drain Current (Note 6) V _{GS} = -2.7V	ID	-0.15 -0.12	А		
Pulsed Drain Current T _P ≤ 300µs, Duty Cycle = 2%)	I _{DM}	-0.5	А		

Thermal Characteristics

Characteristic	Symbol	Value	Units		
Total Dawar Dissination	(Note 5)	Б	0.33	W	
Total Power Dissipation	(Note 6)	P _D	0.45	VV	
Thermal Desistance, Junction to Ambient	(Note 5)	Б	376		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	275	°C/W	
Thermal Resistance, Junction to Case	R ₀ JC	81			
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

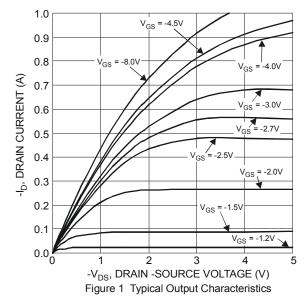
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

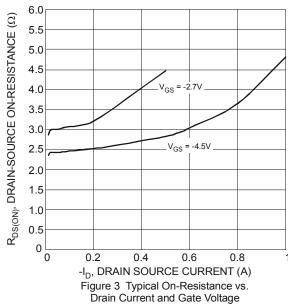
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-25	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	-100	nA	V_{GS} = -8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)				_		
Gate Threshold Voltage	V _{GS(th)}	-0.65	-0.96	-1.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	ם	_	2.5	10	Ω	$V_{GS} = -4.5V, I_D = -0.2A$
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	3	13	1 12	$V_{GS} = -2.7V, I_D = -0.05A$
Forward Transfer Admittance	Y _{fs}	_	189	_	ms	V _{DS} = -5V, I _D = -0.2A
Diode Forward Voltage (Note 7)	V_{SD}	_	_	-1.5	V	V _{GS} = 0V, I _S = -0.2A
DYNAMIC CHARACTERISTICS (Note 8)				•	•	
Input Capacitance	C _{iss}	_	27.2	_		
Output Capacitance	Coss	_	6.1	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	1.7	_		1 - 1.0WH12
Total Gate Charge	Qg	_	0.35	_		
Gate-Source Charge	Q _{gs}	_	0.08	_	nC	$V_{DS} = -5V, I_D = -0.2A,$ $V_{GS} = -4.5V,$
Gate-Drain Charge	Q _{gd}	_	0.06	_		V _{GS} 4.5V,
Turn-On Delay Time	t _{d(on)}	_	4.5	_		
Rise Time	t _r	_	2.3	_		V _{GS} = -4.5V, V _{DD} = -6V
Turn-Off Delay Time	t _{d(off)}	_	24.1	_	ns	$I_D = -0.2A, R_G = 50\Omega$
Fall Time	t _f	_	11.0	_		

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







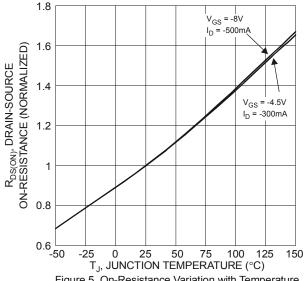
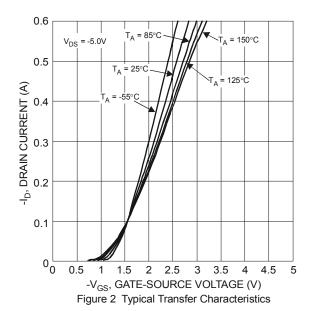
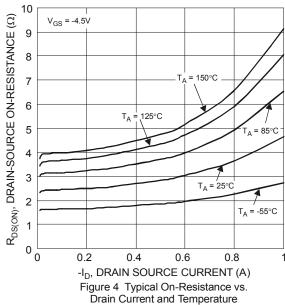
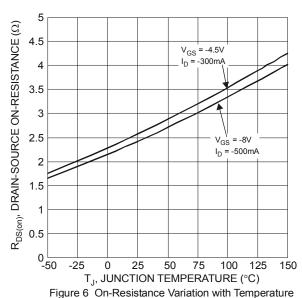


Figure 5 On-Resistance Variation with Temperature









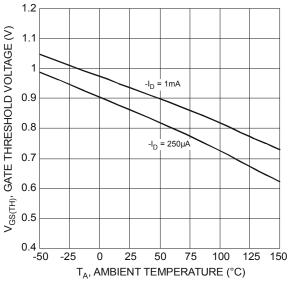
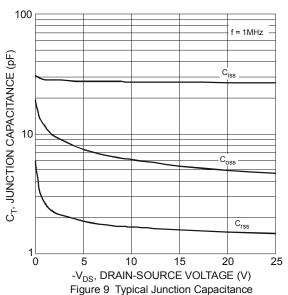
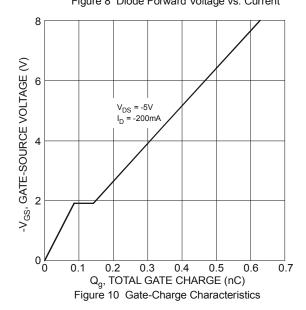
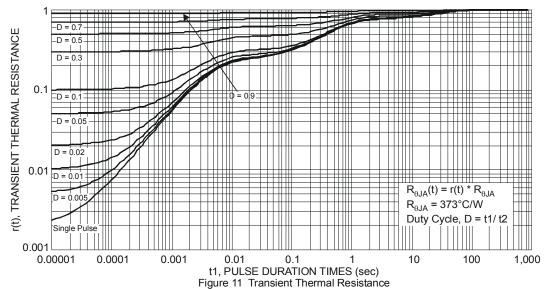


Figure 7 Gate Threshold Variation vs. Ambient Temperature



1 0.8 -I_S, SOURCE CURRENT (A) 0.6 0.4 T_A= 25°C 0.2 0 0 0.3 0.6 0.9 1.2 1.5 $-V_{SD}$, SOURCE-DRAIN VOLTAGE (V) Figure 8 Diode Forward Voltage vs. Current

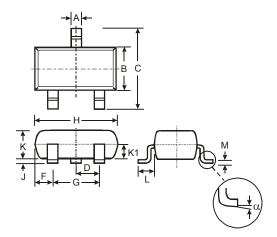






Package Outline Dimensions

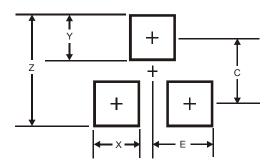
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	ı	0.400					
L	0.45	0.61	0.55					
M	0.085	0.18	0.11					
α	0°	8°	-					
All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
Z	2.9			
Х	0.8			
Y	0.9			
С	2.0			
Е	1.35			



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